

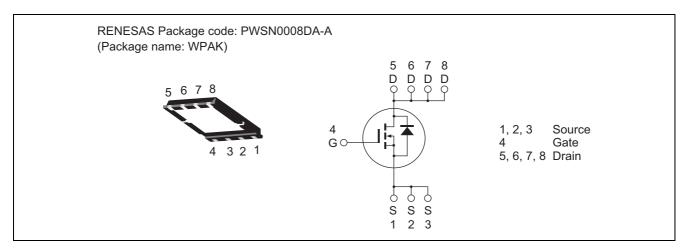
# Silicon N Channel Power MOS FET Power Switching

REJ03G1549-0400 Rev.4.00 Jun 13, 2007

### **Features**

- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance  $R_{DS(on)} = 10 \ m\Omega \ typ. \ (at \ V_{GS} = 10 \ V)$

## **Outline**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	80	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	30	А
Drain peak current	I <sub>D(pulse)</sub> Note1	120	Α
Body-drain diode reverse drain current	I <sub>DR</sub>	30	Α
Avalanche current	I <sub>AP</sub> Note 2	25	А
Avalanche energy	E <sub>AR</sub> Note 2	83	mJ
Channel dissipation	Pch Note3	25	W
Channel to Case Thermal Impedance	θch-c Note3	5	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$
- 3.  $Tc = 25^{\circ}C$

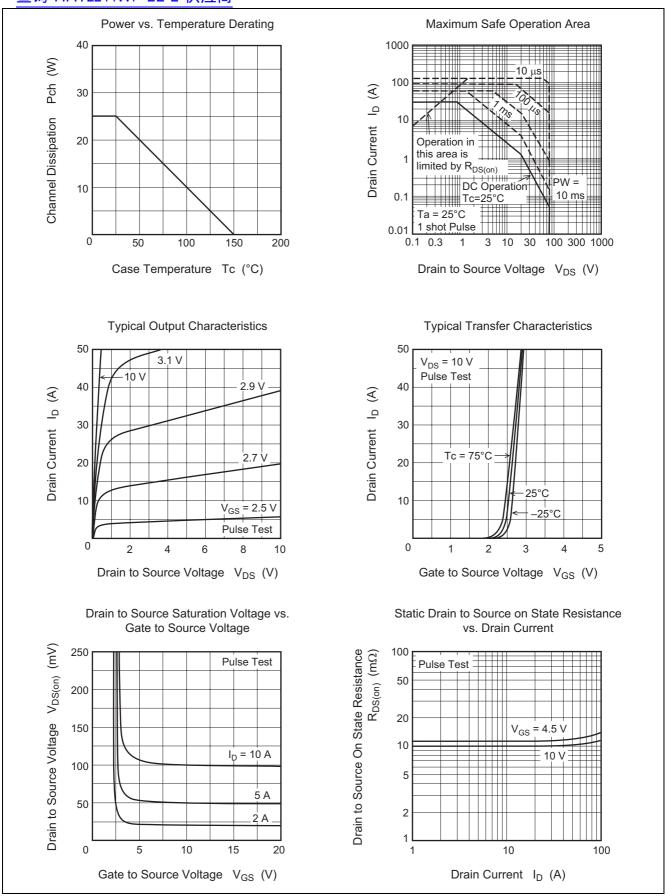
## Electrical Characteristics应商

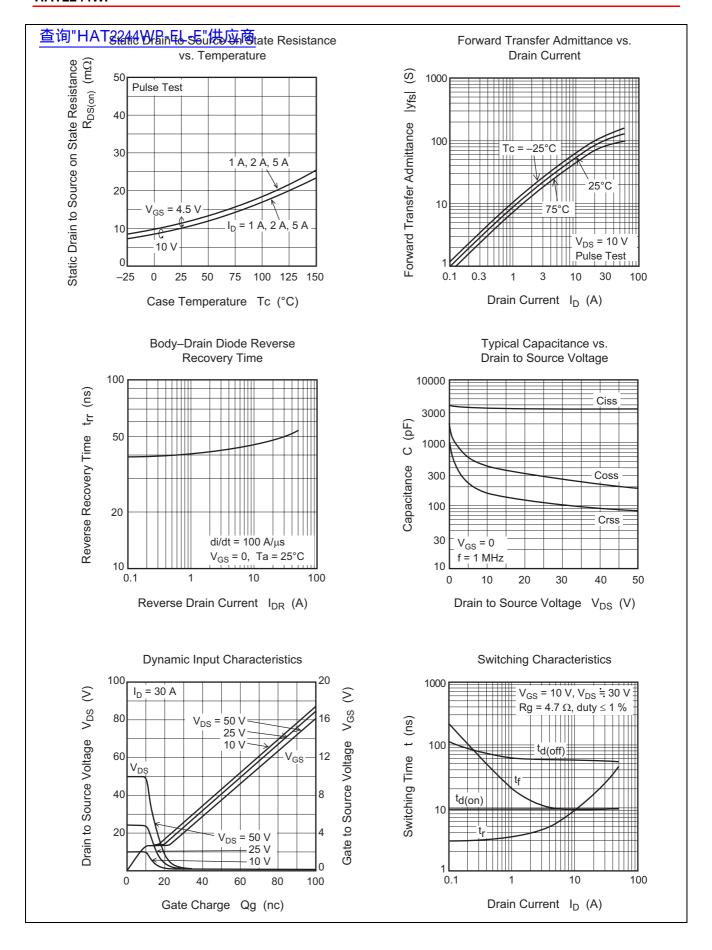
 $(Ta = 25^{\circ}C)$ 

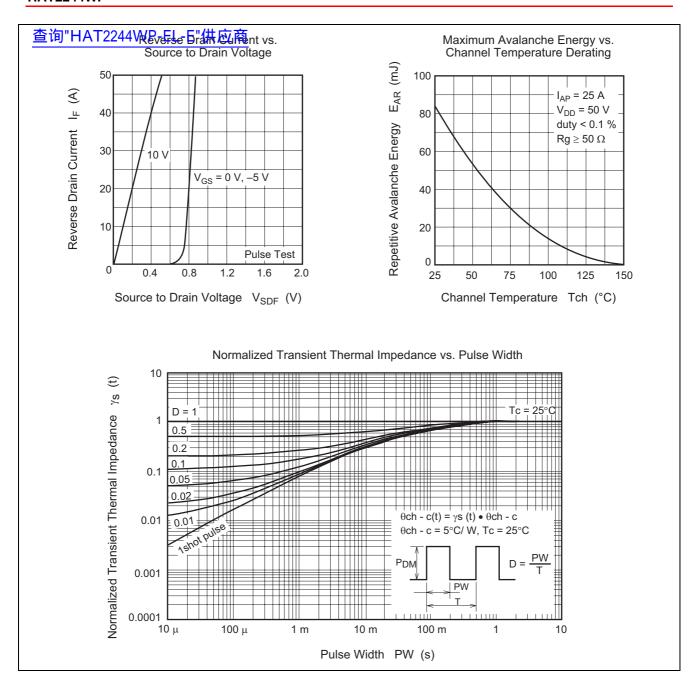
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	80	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	± 0.5	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 80 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0.8	_	2.3	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state	R <sub>DS(on)</sub>	_	10	12.5	mΩ	$I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance	R <sub>DS(on)</sub>	_	11.5	15.5	mΩ	$I_D = 15 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y <sub>fs</sub>	42	70	_	S	$I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	3520	_	pF	V <sub>DS</sub> = 10 V
Output capacitance	Coss	_	410	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	160	_	pF	f = 1 MHz
Gate Resistance	Rg	_	1.2	_	Ω	
Total gate charge	Qg	_	60	_	nC	V <sub>DD</sub> = 25 V
Gate to source charge	Qgs	_	9.5	_	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	_	9.0	_	nC	$I_D = 30 \text{ A}$
Turn-on delay time	t <sub>d(on)</sub>	_	9.5	_	ns	$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$
Rise time	t <sub>r</sub>	_	14.5	_	ns	$V_{DD} \cong 30 \text{ V}$
Turn-off delay time	t <sub>d(off)</sub>	_	56	_	ns	$R_L = 2 \Omega$
Fall time	t <sub>f</sub>	_	9.5	_	ns	$Rg = 4.7 \Omega$
Body-drain diode forward voltage	$V_{DF}$	_	0.83	1.08	V	$I_F = 30 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	50	_	ns	$I_F = 30 \text{ A}, V_{GS} = 0$
						$di_F/dt = 100 A/\mu s$

Notes: 4. Pulse test

## Main Characteristics E"供应商

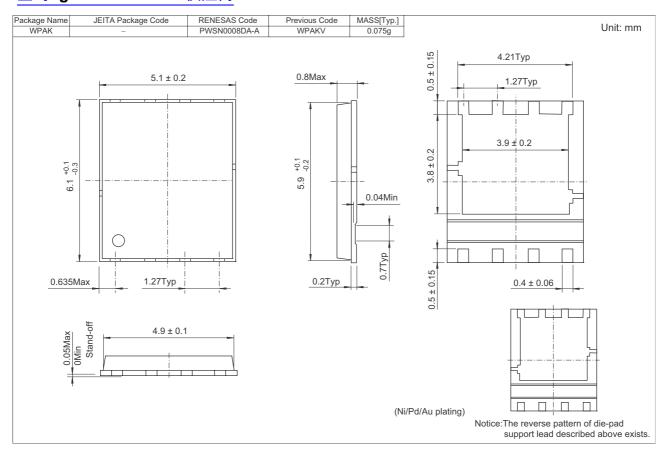






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## Package DimensionsE"供应商



## **Ordering Information**

Part No.	Quantity	Shipping Container
HAT2244WP-EL-E	2500pcs	Taping

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